# P-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)			
-40	0.011 at V <sub>GS</sub> = -10 V	-48			
	0.016 at V <sub>GS</sub> = -4.5 V	-40			

## FEATURES

- EAI UREJ
- DT-Trench Power MOSFET
- + 100 %  $\rm R_g$  and UIS Tested

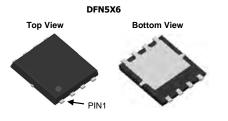
### APPLICATIONS

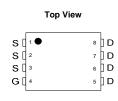
- Notebook
  - Load Switch

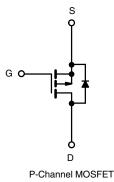


**DTQ6411** 









PARAMETER		SYMBOL	Limit	UNIT
Drain-Source Voltage		V <sub>DS</sub>	- 40	
Gate-Source Voltage		V <sub>GS</sub>	± 20	V
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C		- 48	
	T <sub>A</sub> = 70 °C	I <sub>D</sub>	- 35	
Pulsed Drain Current		I <sub>DM</sub>	- 190	A
Continuous Source Current (Diode Conduction) <sup>a</sup>		ا <sub>S</sub>	- 48	
Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	- 35	
Single Pulse Avalanche Energy		E <sub>AS</sub>	113	mJ
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C	P <sub>D</sub>	39	w
	T <sub>A</sub> = 70 °C	ГD	25	vv
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Soldering Recommendations (Peak Temperature) b, c			260	U

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT	
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 10 s	R <sub>thJA</sub>	20	25		
Maximum Junction-to-Ambient ~	Steady State		25	35	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	2.1	3.3		

#### Notes

a. Surface mounted on 1" x 1" FR4 board.

b. TheDFN5x6isa lea<u>dlesspackage.The endof thel</u>ead terminalisexposedcopper (not plated) as a result of thesingulation process in manufacturing. A solderfillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequatebottom side solder interconnection.

c. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP	MAX.	LINUT	
	STMBOL	TEST CONDITIONS	WIIN.	TYP.	WAX.	UNIT	
Static							
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = -250 \ \mu A$	-1	-	-3	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ = ± 20 V	-	-	± 100	nA	
Zero Gate Voltage Drain Current	1	$V_{DS} = -32 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	-	-1	μΑ	
	IDSS	$V_{DS}$ = -32 V, $V_{GS}$ = 0 V, $T_J$ = 70 °C	-	-	-10		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le$ -5 V, $V_{GS}$ = -10 V	-60	-	-	А	
Drain-Source On-State Resistance <sup>a</sup>	D	$V_{GS} = -10 \text{ V}, \text{ I}_{D} = -5 \text{ A}$	-	0.011	0.014	Ω	
	R <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -3 \text{ A}$	-	0.016	0.022		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = -15 \text{ V}, \text{ I}_{D} = -5 \text{ A}$	-	35	-	S	
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	$I_{\rm S}$ = -4.5 A, $V_{\rm GS}$ = 0 V	-	-0.7	-1.2	V	
Dynamic <sup>b</sup>							
Input Capacitance	Ciss	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 100 V,	-	2120	-	pF	
Output Capacitance	C <sub>oss</sub>		-	230	-		
Reverse Transfer Capacitance	C <sub>rss</sub>	f = 1 MHz	-	180	-		
Total Gate Charge	Qg		-	121	-		
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> = -20 V, V <sub>GS</sub> = -10 V, I <sub>D</sub> = -5 A	-	20	-	nC	
Gate-Drain Charge	Q <sub>gd</sub>		-	32	-		
Gate Resistance	R <sub>g</sub>		-	1.5	-	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>		-	21	-		
Rise Time	tr	$\label{eq:VDD} \begin{array}{l} V_{\text{DD}} = \text{-20 V},  R_{\text{L}} = \text{30 } \Omega \\ I_{\text{D}} \cong \text{-5 A},  V_{\text{GEN}} = \text{-10 V},  R_{\text{g}} = 6 \; \Omega \end{array}$	-	20	-	1	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	55	-	ns	
Fall Time	t <sub>f</sub>		-	12	-		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	l⊧ = -4.5 A. dl/dt = 100 A/us	-	29	50		

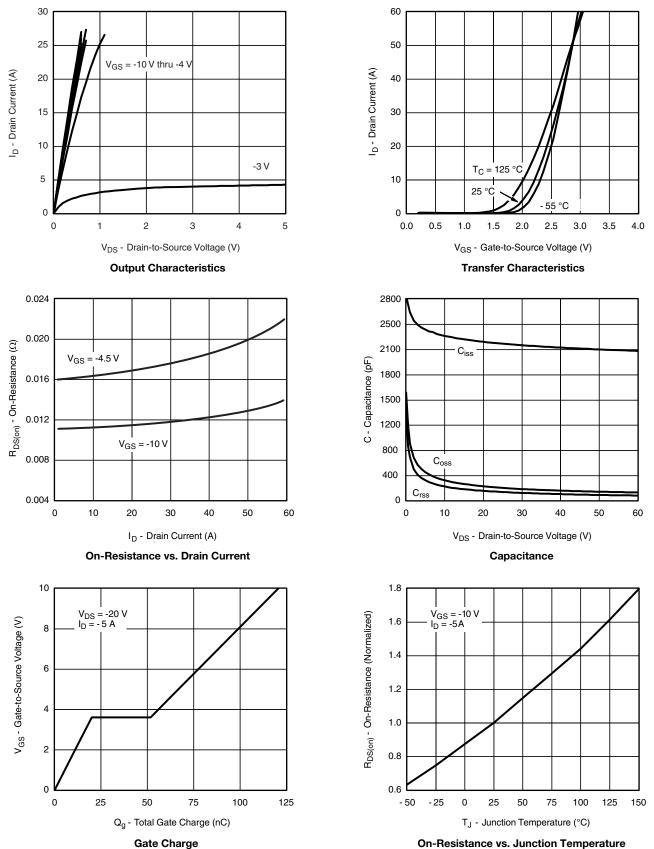
#### Notes

a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$ 

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

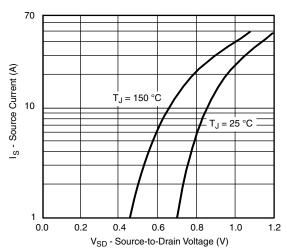




#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

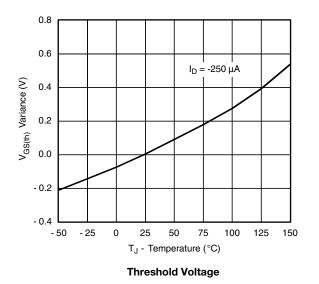


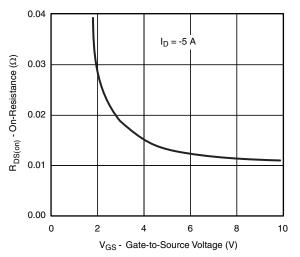




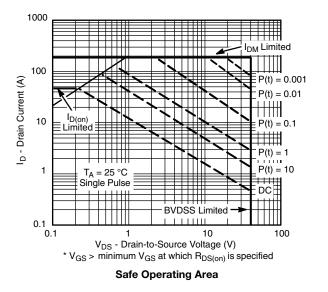
### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Source-Drain Diode Forward Voltage



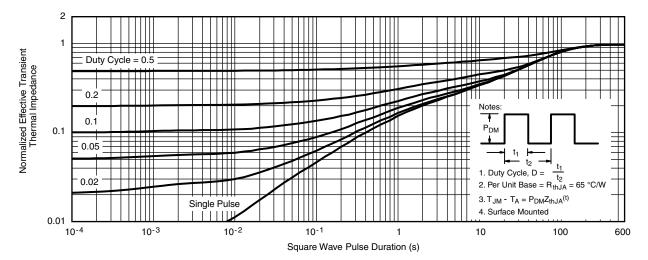


**On-Resistance vs. Gate-to-Source Voltage** 

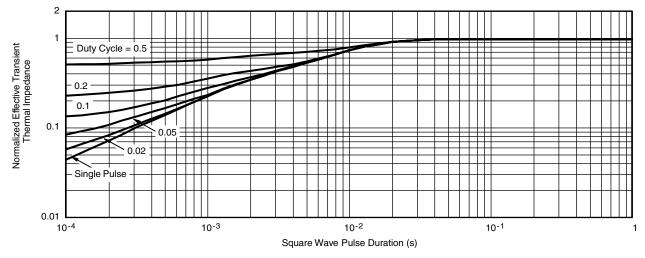




### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case



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